鼎德丰
DING DE FENG

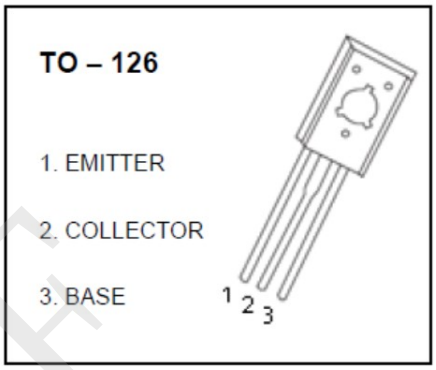
NPN Silicon Transistor

2SC2912

- **Complementary to 2SA1210**
- **Package: TO-126**

Maximum Ratings (Ta = 25℃)

Parameter	Symbol	Rating		Unit
Collector-base voltage	BV_{CBO}	200		V
Collector-emitter voltage	BV_{CEO}	200		V
Emitter-base voltage	BV_{EBO}	5		V
Collector current	I_C	140		mA
Peak Collector current	I_{CP}	200		mA
Collector Power Dissipation	P_C	1		W
	P_C	Ta = 25℃	20	
Junction Temperature	Tj	150		℃
Storage Temperature	Tstg	-55～+150		℃



Electrical Characteristics（Ta=25℃）

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BV_{CBO}	I_C=1mA，I_E=0	200			V
Collector-Emitter Breakdown Voltage	BV_{CEO}	I_C=10mA，I_B=0	200			V
Emitter-Base Breakdown Voltage	BV_{EBO}	I_E=1mA，I_C=0	5			V
collector-base cut-off current	I_{CBO}	V_{CB}=160V，I_E=0			1	μA
emitter-base cut-off current	I_{EBO}	V_{EB}=4V，I_C=0			1	μA
DC current gain	H_{FE1}	V_{CE}=5V，I_C=10mA	100		400	
collector-emitter saturation voltage	V_{CESAT}	I_C=50mA，I_B=5mA			0.4	V
Base-Emitter Voltage	V_{BE}	V_{CE}=5V，I_C=10mA			1.2	
Transition frequency	f_T	V_{CE}=10V，I_C=10 mA		150		MH_Z

Classification of H_{FE}

Rank	R	S	T
Range	100-200	140-280	200-400